

## 700V GaN Power Transistor

### **Description**

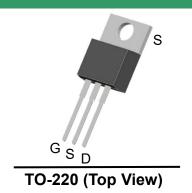
| Product Summary     |                            |                    |  |  |
|---------------------|----------------------------|--------------------|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}(m\Omega)(Typ)$ | I <sub>D</sub> (A) |  |  |
| 700                 | 180                        | 13                 |  |  |

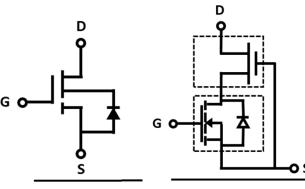
### **Feature**

- > Easy to use, compatible with standard gate drivers
- ightharpoonup Excellent  $Q_G \times R_{DS(on)}$  figure of merit (FOM)
- ightharpoonup Low  $\mathbf{Q}_{\mathrm{RR}}$ , no free-wheeling diode required
- Low switching loss
- > RoHS compliant and Halogen-free

### **Applications**

- High efficiency power supplies
- > Telecom and datacom
- > Automotive
- Servo motors





**Schematic Symbol** 

Cascode Device Structure

### Absolute maximum rating@25°C

| Parameter                                    |                       | Symbol                           | Rating     | Unit |  |
|--|-----------------------|----------------------------------|------------|------|--|
| Drain-Source Voltage                         |                       | V <sub>DS</sub>                  | 700        | V    |  |
| Gate-Source Voltage                          |                       | V <sub>GS</sub>                  | ±20        | V    |  |
| Transient Drain-Source Voltage <sup>1)</sup> |                       | V <sub>TDS</sub>                 | 800        | V    |  |
| Continuous Drain Current                     | T <sub>C</sub> =25°C  |                                  | 13         | А    |  |
| Continuous Drain Current                     | T <sub>C</sub> =100°C | - I <sub>D</sub>                 | 8          |      |  |
| Dulgged Drain Comment (Dulgge Midths 40000)  | T <sub>C</sub> =25°C  |                                  | 41         | А    |  |
| Pulsed Drain Current (Pulse Width: 100µs)    | T <sub>C</sub> =150°C | I <sub>DM</sub>                  | 30         |      |  |
| Power Dissipation                            |                       | P <sub>D</sub>                   | 57         | W    |  |
| Soldering Peak Temperature                   |                       | T <sub>CSOLD</sub>               | 260        | °C   |  |
| Operating Junction and Storage Temperature   |                       | T <sub>J,</sub> T <sub>STG</sub> | -55 to 150 | °C   |  |

### **Thermal Resistance**

| Parameter   | Symbol          | Min | Тур | Max | Unit |
|---|-----------------|-----|-----|-----|------|
| Thermal Resistance, Junction-to-Case                  | $R_{	heta JC}$  | -   | 2.2 | -   | °C/W |
| Thermal Resistance, Junction-to-Ambient <sup>2)</sup> | $R_{\theta JA}$ | -   | 50  | -   | °C/W |

# Electrical characteristics per line@25°C (unless otherwise specified)

| Parameter                                      | Symbol                     | Conditions  |                        | Min.                 | Тур.  | Max. | Units |
|--|----------------------------|---|------------------------|----------------------|-------|------|-------|
| Statistic Characteristics                      |                            |   |                        |                      |       |      |       |
| Maximum Drain-Source Voltage                   | V <sub>DS-Max</sub>        | V <sub>GS</sub> :                                 | = 0V                   | 700                  | -     | -    | V     |
| Drain-Source Breakdown Voltage                 | BV <sub>DSS</sub>          | $V_{GS} = 0V, I_{D} = 250\mu A$                   |                        | -                    | 1000  | -    | V     |
| Zoro Cata Valtaga Drain Current                |                            | V <sub>DS</sub> =700V,<br>V <sub>GS</sub> =0V     | T <sub>J</sub> =25°C   | -                    | 5     | 20   | μА    |
| Zero Gate Voltage Drain Current                | I <sub>DSS</sub>           |   | T <sub>J</sub> =150°C  | -                    | 50    | -    |       |
| Gate-Body Leakage Current                      | I <sub>GSS</sub>           | $V_{GS} = \pm 20V, V_{DS} = 0V$                   |                        | ı                    | -     | ±150 | nA    |
| Gate Threshold Voltage                         | $V_{GS(th)}$               |   |                        | 3                    | 4     | 5    | V     |
| Gate threshold voltage temperature coefficient | $\triangle V_{GS(th)}/T_J$ | $V_{DS} = V_{GS}$                                 | l <sub>D</sub> = 500μA | -                    | -10.7 | -    | mV/°C |
| Drain-Source On-State Resistance <sup>3)</sup> | R                          | V <sub>GS</sub> =12V,<br>I <sub>D</sub> =4A       | T <sub>J</sub> =25°C   | -                    | 180   | 225  | - mΩ  |
| Brain-Godice On-State Resistance               | R <sub>DS(ON)</sub>        | I <sub>D</sub> =4A                                | T <sub>J</sub> =150°C  | -                    | 360   | -    |       |
| Dynamic Characteristics                        |                            |   |                        |                      |       |      |       |
| Input Capacitance                              | C <sub>lss</sub>           | $V_{DS} = 400V, V_{GS} = 0V,$<br>f = 1MHz         |                        | -                    | 515   | -    | pF    |
| Output Capacitance                             | C <sub>oss</sub>           |   |                        | -                    | 23    | -    |       |
| Reverse Transfer Capacitance                   | C <sub>rss</sub>           |   |                        | ı                    | 1.2   | -    |       |
| Effective Output Capacitance, Energy Related   | C <sub>o(er)</sub>         | V <sub>GS</sub> = 0V,<br>V <sub>DS</sub> = 0-400V |                        | ı                    | 35    | -    | nE    |
| Effective Output Capacitance, Time Related     | C <sub>o(tr)</sub>         |   |                        | ı                    | 86    | -    | pF    |
| Output Charge                                  | Q <sub>oss</sub>           |   |                        | ı                    | 34.5  | -    | nC    |
| Turn-on Delay Time                             | t <sub>d(on)</sub>         |   |                        | ı                    | 43    | -    | ns    |
| Turn-on Rise Time                              | t <sub>r</sub>             | $V_{DS} = 400V, I_D = 3A,$                        |                        | ı                    | 15    | -    |       |
| Turn-Off Delay Time                            | t <sub>d(off)</sub>        | $V_{GS} = 0-12V, R_G = 47\Omega$                  |                        | -                    | 39    | -    |       |
| Turn-Off Fall Time                             | t <sub>f</sub>             | 1   |                        | ı                    | 11    | -    |       |
| Total Gate Charge                              | $Q_g$                      | $V_{DS} = 400V, I_{D} = 6A,$<br>$V_{GS} = 0-12V$  |                        | -                    | 15    | -    |       |
| Gate-Source Charge                             | $Q_{gs}$                   |   |                        | 1                    | 4.9   | -    | nC    |
| Gate-Drain Charge                              | $Q_{gd}$                   |   |                        | 1                    | 5.5   | -    |       |
| Reverse Diode Characteristics                  |                            |   |                        |                      |       |      |       |
|  | V <sub>SD</sub>            | V <sub>GS</sub> =0V                               | ′, I <sub>S</sub> =4A  | ı                    | 1.3   | -    |       |
| Diode Forward Voltage                          |                            | V <sub>SD</sub>                                   | V <sub>GS</sub> =0V,   | T <sub>J</sub> =25°C | -     | 1.8  | -     |
|  |                            | I <sub>S</sub> =8A                                | T <sub>J</sub> =150°C  | -                    | 3     | -    |       |
| Reverse Recovery Time                          | t <sub>rr</sub>            | V <sub>GS</sub> =0V                               |                        | -                    | 18    | -    | ns    |
| Reverse Recovery Charge                        | Q <sub>rr</sub>            | - V <sub>DD</sub> =400V,<br>di/dt=1000A/μs        |                        | -                    | 34.5  | -    | μC    |

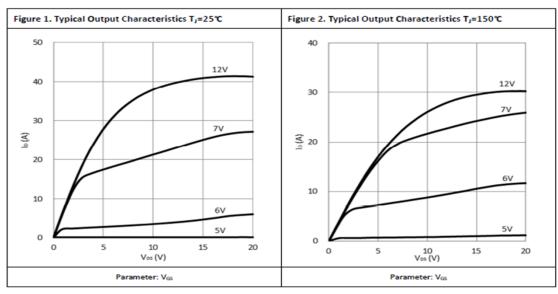
Notes:

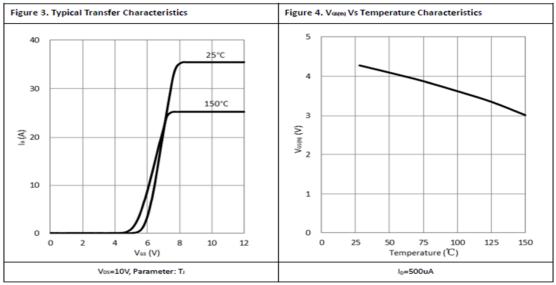
<sup>1.</sup> Off-state spike duty cycle < 0.01, spike duration < 2μs

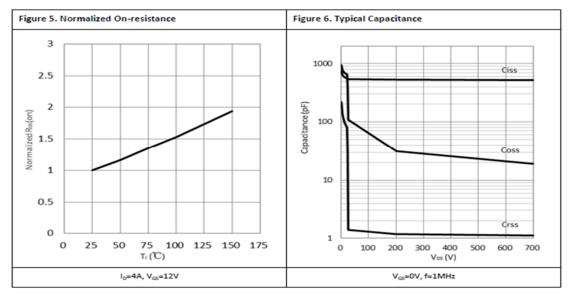
<sup>2.</sup> Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm²copper area and 70µm thickness)

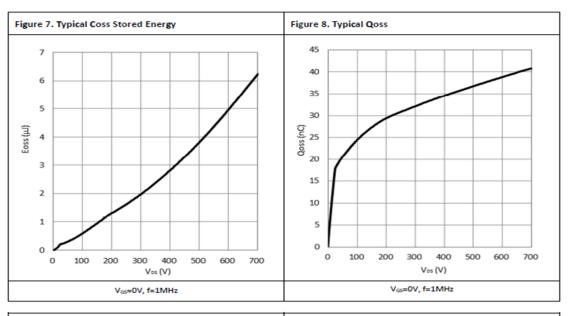
<sup>3.</sup> Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

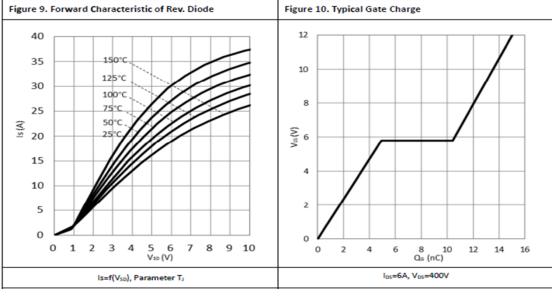
## **Typical Characteristics**

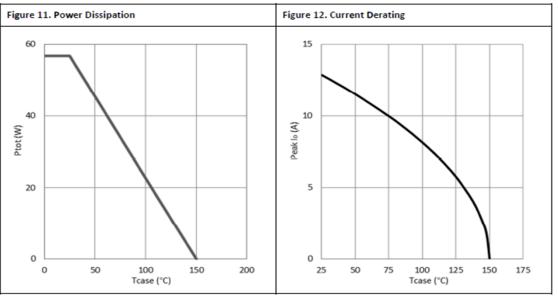


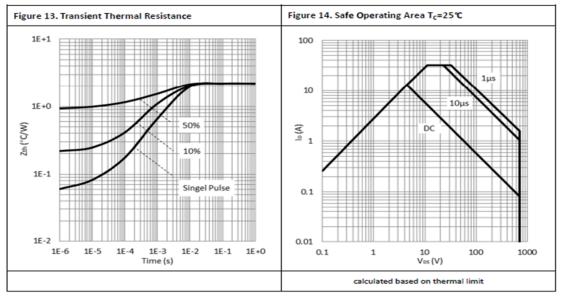


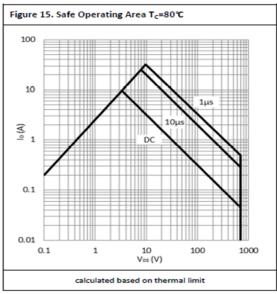




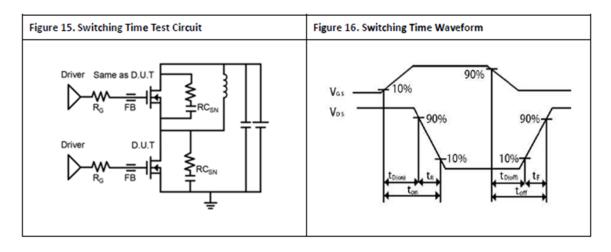


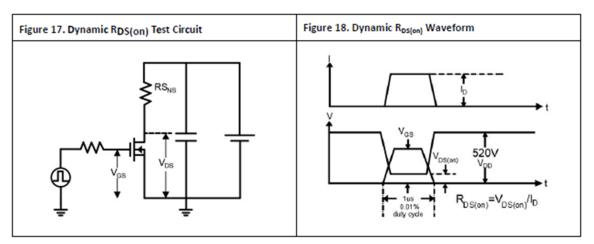


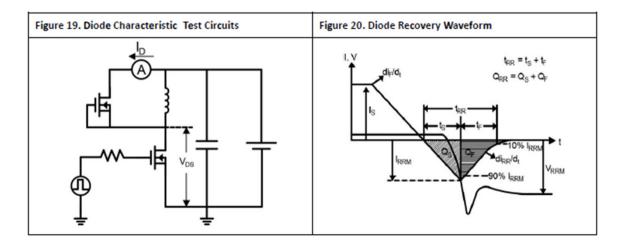




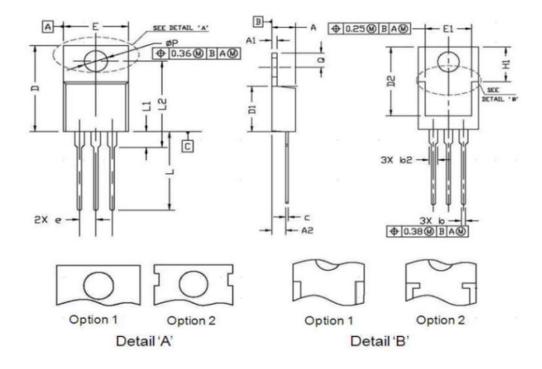
## **Test Circuits and Waveforms**







## **Product Dimension (TO-220)**



| OVMDOL | Millimeter |       |  |  |  |
|--------|------------|-------|--|--|--|
| SYMBOL | Min        | Max   |  |  |  |
| А      | 4.30       | 4.80  |  |  |  |
| A1     | 1.20       | 1.45  |  |  |  |
| A2     | 2.20       | 2.90  |  |  |  |
| b      | 0.69       | 0.95  |  |  |  |
| b2     | 1.00       | 1.60  |  |  |  |
| С      | 0.33       | 0.65  |  |  |  |
| D      | 14.70      | 16.20 |  |  |  |
| D1     | 8.59       | 9.65  |  |  |  |
| D2     | 11.75      | 13.60 |  |  |  |
| е      | 2.54BSC    |       |  |  |  |
| E      | 9.60       | 10.60 |  |  |  |
| E1     | 7.00       | 8.46  |  |  |  |
| H1     | 6.20       | 7.00  |  |  |  |
| L      | 12.60      | 14.80 |  |  |  |
| L1     | 2.70       | 3.80  |  |  |  |
| L2     | 12.13      | 16.50 |  |  |  |
| Q      | 2.40       | 3.10  |  |  |  |
| Р      | 3.50 3.90  |       |  |  |  |

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